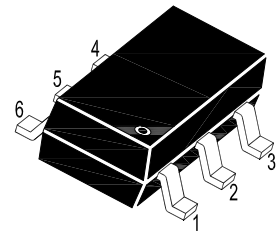
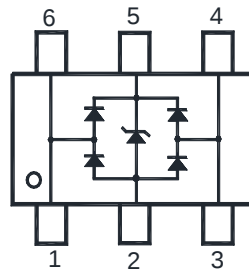


E5V0LUD2H

ESD Protection Array Diode

Features

- Low leakage current
- Low capacitance



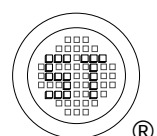
1. I/O1 2. GND 3. I/O2
4. I/O2 5. Vcc 6. I/O1
Marking Code : F9
SOT-26 Plastic package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
IEC61000-4-2 (ESD) Air Contact	V_{ESD}	± 15 ± 15	KV
Operating Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Stand-Off Voltage	V_{RWM}	-	5	V
Reverse Breakdown Voltage at $I_R = 1 \text{ mA}$	$V_{(\text{BR})R}$	6	9	V
Reverse Current at $V_R = 5 \text{ V}$	I_R	-	0.2	μA
Forward Voltage at $I_F = 10 \text{ mA}$	V_F	-	1.1	V
Clamping Voltage at $I_{\text{PP}} = 1 \text{ A}$, $t_p = 8/20 \mu\text{s}$, Any I/O pin to GND at $I_{\text{PP}} = 5 \text{ A}$, $t_p = 8/20 \mu\text{s}$, Any I/O pin to GND	V_C	- -	12 17	V
Capacitance Between I/O and GND at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, Any I/O pin to GND	$C_{\text{I/O-GND}}$	-	1.2	pF
Capacitance Between I/O at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, between I/O, GND not connected	$C_{\text{I/O-I/O}}$	-	1.2	pF



Electrical characteristic curves

Fig 1. Pulse Waveform

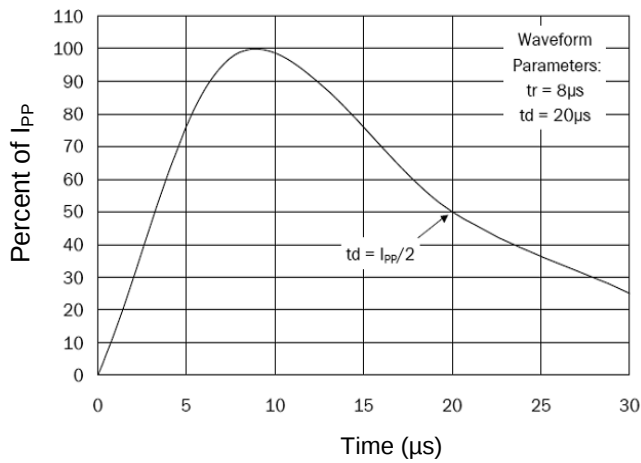


Fig 2. Power Derating Curve

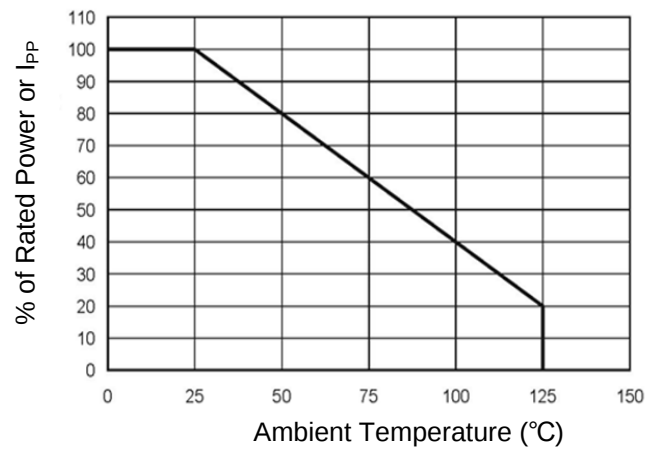


Fig 3. Clamping Voltage Curve

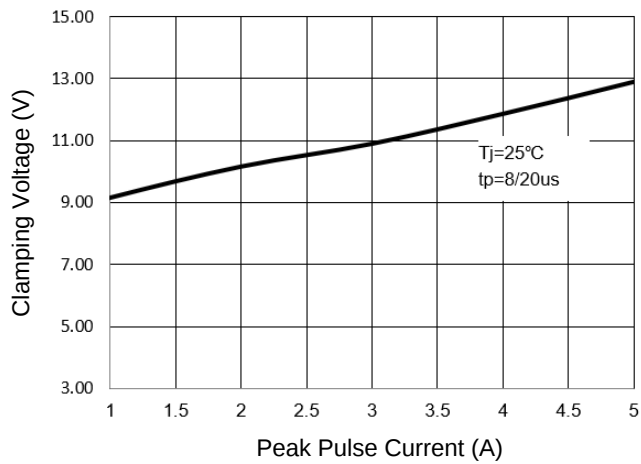


Fig 4. Junction Capacitance

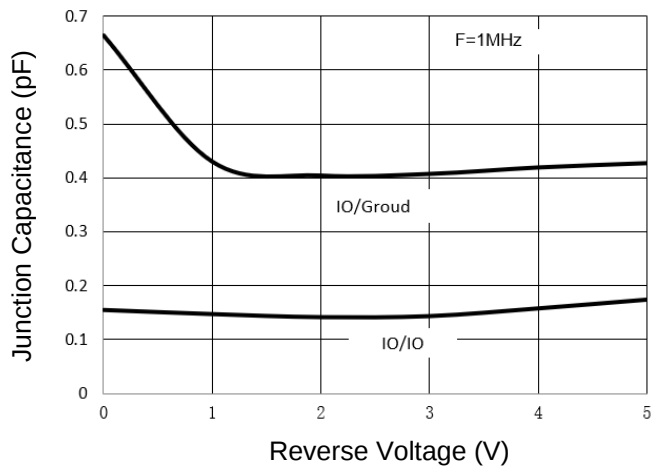
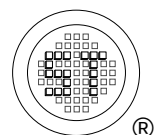
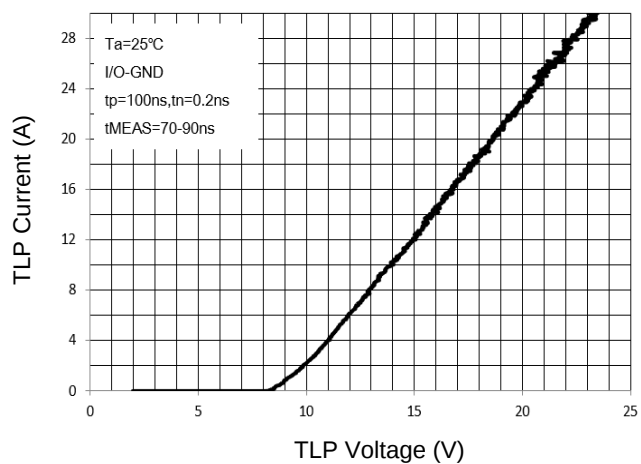


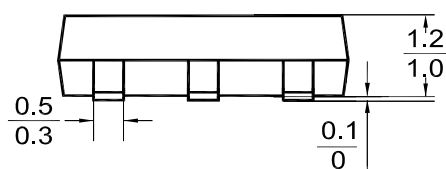
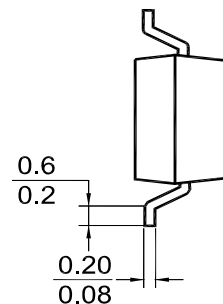
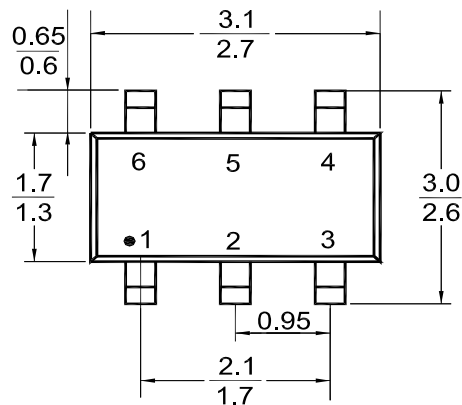
Fig 5 TLP Curve



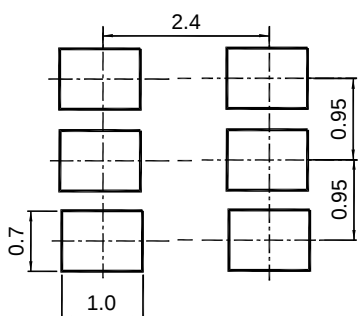
E5V0LUD2H

Package Outline Dimensions (Units: mm)

SOT-26



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-26	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

"F9" = Part No.
"YM" = Date Code Marking
"Y" = Year
"M" = Month
Font type: Arial

